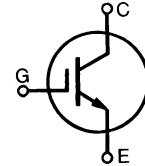
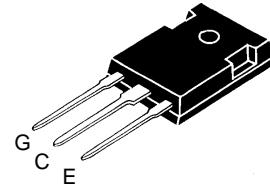


**Low  $V_{CE(sat)}$   
High speed IGBT**
**IXGH 25 N120  
IXGH 25 N120A**

$V_{CES}$	$I_{C25}$	$V_{CE(sat)}$
1200 V	50 A	3 V
1200 V	50 A	4 V



Symbol	Test Conditions	Maximum Ratings		
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V	
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	1200	V	
$V_{GES}$	Continuous	$\pm 20$	V	
$V_{GEM}$	Transient	$\pm 30$	V	
$I_{C25}$	$T_C = 25^\circ\text{C}$	50	A	
$I_{C90}$	$T_C = 90^\circ\text{C}$	25	A	
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	100	A	
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 33 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 50$ @ 0.8 $V_{CES}$	A	
$P_c$	$T_C = 25^\circ\text{C}$	200	W	
$T_J$		-55 ... +150	$^\circ\text{C}$	
$T_{JM}$		150	$^\circ\text{C}$	
$T_{stg}$		-55 ... +150	$^\circ\text{C}$	
$M_d$	Mounting torque (M3)	1.13/10	Nm/lb.in.	
<b>Weight</b>		6	g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$	

**TO-247 AD**


G = Gate,  
E = Emitter,  
C = Collector,  
TAB = Collector

**Features**

- International standard package JEDEC TO-247 AD
- 2nd generation HDMOS™ process
- Low  $V_{CE(sat)}$ 
  - for low on-state conduction losses
- MOS Gate turn-on
  - drive simplicity

**Applications**

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge systems
- Solid state relays

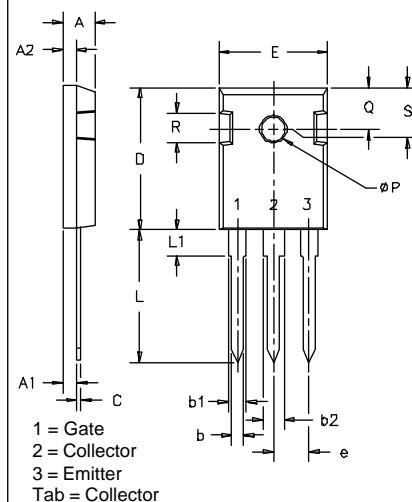
**Advantages**

- Easy to mount with 1 screw (TO-247)  
(isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
$BV_{CES}$	$I_C = 3 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$ , $V_{CE} = V_{GE}$	2.5	6	V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	250 1	$\mu\text{A}$ mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$		$\pm 100$	nA
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$	25N120 25N120A	3 4	V

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10 \text{ V}$ , Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $\leq 2\%$	8	15	S
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	2750	pF	
$C_{oes}$		200	pF	
$C_{res}$		50	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.5 V_{CES}$	130	180	nC
$Q_{ge}$		25	50	nC
$Q_{gc}$		55	90	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $L = 100 \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 33 \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	100		ns
$t_{ri}$		250		ns
$t_{d(off)}$		650	1000	ns
$t_{ri}$		700		ns
$E_{off}$		600	800	ns
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $L = 100 \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 33 \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$	100		ns
$t_{ri}$		250		ns
$E_{on}$		4.2		mJ
$t_{d(off)}$		720	1000	ns
$t_{ri}$		1200		ns
$E_{off}$		800	1200	ns
$R_{thJC}$		15		mJ
$R_{thCK}$			0.62	K/W
			0.25	K/W

TO-247 AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A <sub>1</sub>	.087	.102	2.2	2.54
A <sub>2</sub>	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b <sub>1</sub>	.065	.084	1.65	2.13
b <sub>2</sub>	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215	BSC	5.45	BSC
L	.780	.800	19.81	20.32
L <sub>1</sub>	.177			4.50
ØP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242	BSC	6.15	BSC

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025